

EW-432

Shipped in packet-tape reel(5000pcs/Reel)

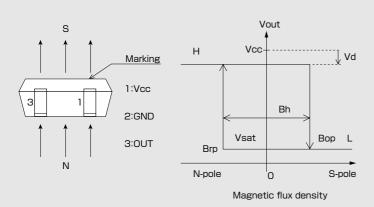
EW-432 is composed of a Ultra-high sensitive InSb Hall element and a signal processing IC chip in a package.

Bipolar Hall Effect Latch Supply Voltage 2.2~18V

Hall Element Continuous Excitation High Sensitivity Bop:3mT Output With Pull-up Resistor SMT

Notice: It is requested to read and accept "IMPORTANT NOTICE" written on the back of the front cover of this catalogue.

Operational Characteristics



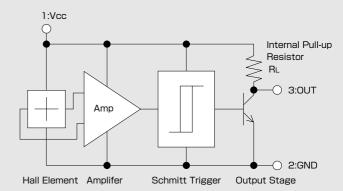


● Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Limit	Unit	
Supply Voltage	V _{cc}	18**	V	
Output H Voltage	V _{o(off)}	V _{cc}	V	
Output L Current	Isink	12	mA	
Operating Temperature Range	Topr	−30 ~ 115	°C	
Storage Temperature Range	Tstg	−40 ~ 125	°C	

 $^{(*) \ \}mathsf{Please} \ \mathsf{refer} \ \mathsf{to} \ \mathsf{Supply} \ \mathsf{Voltage} \ \mathsf{Derating} \ \mathsf{Curve}.$

•Functional Block Diagram



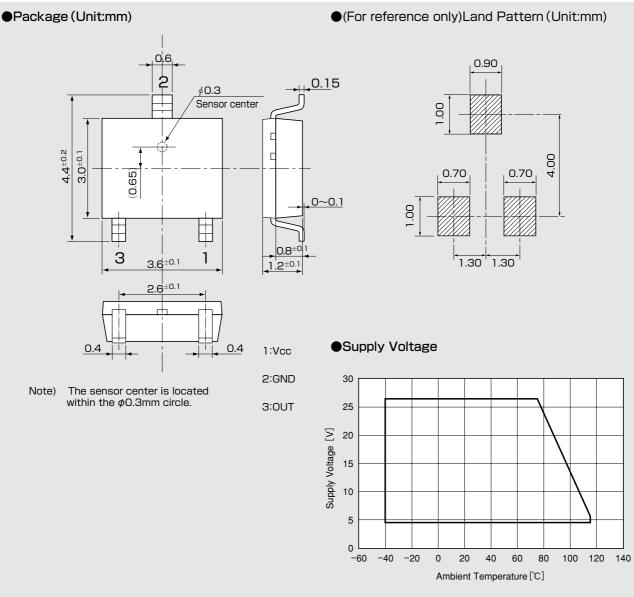
● Magnetic and Electrical Characteristics (Ta=25°C)

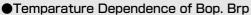
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Supply Voltage	V _{CC}		2.2	12	18	V
Operating Point	B _{OP}	V _{CC} =12V		3	6	mT
Release Point	B _{rp}	V _{CC} =12V	-6	-3		mT
Hysteresis	Bh	V _{CC} =12V		6		mT
Output Saturation Voltage	V _{sat}	V _{CC} =12V,OUT"L"			0.4	٧
Supply Current	I_{CC}	V _{CC} =12V,OUT"H"			8	mA
Output Down Voltage	٧d	V _{CC} =12V,OUT"H"			20	mV
Internal Load Resistance	RL		6		14	kΩ

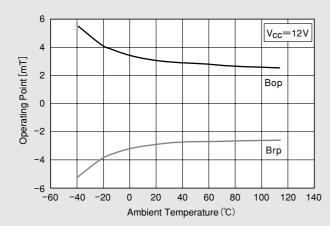
1[mT]=10[Gauss]

•Please be aware that our products are not intended for use in life support equipment, devices, or systems. Use of our products in such applications requires the

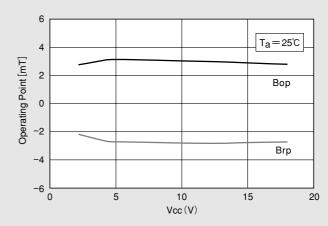
certain applications using semiconductor devices may involve potential risks of personal injury, property damage, or loss of life. In order to minimize these risks, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards. Inclusion of our products in such applications is understood to be fully at the risk of the customer using our devices or systems.







Supply Voltage Dependence of Bop. Brp



С

h

0

p

q